International **10** Rectifier

August, 27th 2009 Automotive grade

AUIPS7121R

CURRENT SENSE HIGH SIDE SWITCH

Features

- Suitable for 24V systems
- Over current shutdown
- Over temperature shutdown
- Current sensing
- Active clamp
- Optimized Turn On/Off for EMI
- Reverse battery protection (Mosfet on)

Applications

- 75W Filament lamp
- Solenoid
- 24V loads for trucks

Description

The AUIPS7121R is a fully protected five terminal high side switch specifically designed for driving lamp. It features current sensing, over-current, over-temperature, ESD protection and drain to source active clamp. When the input voltage Vcc - Vin is higher than the specified threshold, the output power Mosfet is turned on. When the Vcc - Vin is lower than the specified Vil threshold, the output Mosfet is turned off. The Ifb pin is used for current sensing. The over-current shutdown is higher than inrush current of the lamp.

Product Summary

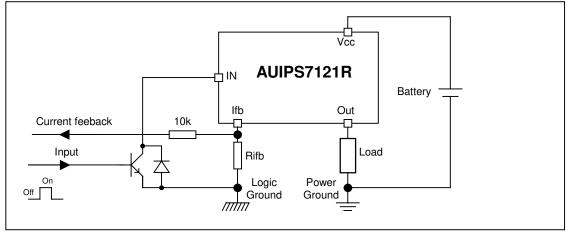
Rds(on) 30 Vclamp Current shutdown

30mΩ max. 65V 1 50A min.

Packages



Typical Connection



Qualification Information⁺

| Qualification Leve | 91 | Automotive (per AEC-Q100 ^{††}) Comments: This family of ICs has passed an Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level. | | | | |
|----------------------------|------------------|--|--|--|--|--|
| Moisture Sensitivity Level | | DPAK-5L | MSL1, 260°C (per IPC/JEDEC J-STD-020) | | | |
| | Machine Model | | Class M2 (200 V) (per AEC-Q100-003) | | | |
| ESD | Human Body Model | Class H1C (1500 V) (per AEC-Q100-002) | | | | |
| Charged Device Model | | Class C5 (1000 V) (per AEC-Q100-011) | | | | |
| IC Latch-Up Test | | Class II, Level A (per AEC-Q100-004) | | | | |
| RoHS Compliant | | Yes | | | | |

Qualification standards can be found at International Rectifier's web site http://www.irf.com/ Exceptions to AEC-Q100 requirements are noted in the qualification report. † ††

Absolute Maximum Ratings Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. (Tambient=25°C unless otherwise specified).

| Symbol | Parameter | Min. | Max. | Units |
|--------------|--|--------|---------|-------|
| Vout | Maximum output voltage | Vcc-60 | Vcc+0.3 | V |
| Vcc-Vin max. | Maximum Vcc voltage | -32 | 60 | V |
| lifb, max. | Maximum feedback current | -50 | 10 | mA |
| Vcc sc | Maximum Vcc voltage with short circuit protection see page 7 | _ | 50 | V |
| Pd | Maximum power dissipation (internally limited by thermal protection) | | | W |
| FU | Rth=50°C/W DPack 6cm ² footprint | _ | 2.5 | vv |
| Tj max. | Max. storage & operating junction temperature | -40 | 150 | °C |

Thermal Characteristics

| Symbol | Parameter | Тур. | Max. | Units |
|--------|--|------|------|-------|
| Rth1 | Thermal resistance junction to ambient DPak Std footprint | 70 | _ | |
| Rth2 | Thermal resistance junction to ambient Dpak 6cm ² footprint | 50 | _ | °C/W |
| Rth3 | Thermal resistance junction to case Dpak | 2 | _ | |

Recommended Operating Conditions

| Symbol | Parameter | Min. | Max. | Units |
|--------|--|------|------|-------|
| lout | Continuous output current, Tambient=85°C, Tj=125°C | | | Δ |
| | Rth=50°C/W, Dpak 6cm ² footprint | _ | 3.8 | ~ |
| Rifb | Ifb resistor | 1.5 | | kΩ |

Static Electrical Characteristics

Tj=25°C, Vcc=28V (unless otherwise specified)

| Symbol | Parameter | Min. | Тур. | Max. | Units | Test Conditions |
|-------------|-------------------------------------|------|------|------|--------|-----------------------|
| Vcc op. | Operating voltage range | 6 | | 60 | V | |
| Rds(on) | ON state resistance Tj=25°C | | 24 | 30 | mΩ | lds=2A |
| | ON state resistance Tj=150°C(2) | _ | 45 | 55 | 1115.2 | IUS=2A |
| Icc off | Supply leakage current | — | 2 | 4 | | Vin=Vcc=28V,Vifb=Vgnd |
| lout off | Output leakage current | — | 2 | 4 | μA | Vout=Vgnd |
| lin on | Input current when device on | 1 | 2.5 | 4 | mA | Vcc-Vin=28V |
| V clamp1 | Vcc to Vout clamp voltage 1 | 60 | 64 | _ | | ld=10mA |
| V clamp2 | Vcc to Vout clamp voltage 2 | 60 | 65 | 72 | v | Id=20A see fig. 2 |
| Vih(1) | High level Input threshold voltage | — | 3.5 | 5.9 | v | ld=10mA |
| Vil(1) | Low level Input threshold voltage | 1.5 | 3.2 | _ | | |
| Rds(on) rev | Reverse On state resistance Tj=25°C | — | 25 | 40 | mΩ | lsd=2A |
| Vf | Forward body diode voltage Tj=25°C | — | 0.75 | 0.85 | V | lf=3A |
| | Forward body diode voltage Tj=125°C | _ | 0.62 | 0.7 | v | |
| Rin | Input resistor | 180 | 250 | 350 | Ω | |

(1) Input thresholds are measured directly between the input pin and the tab.

Switching Electrical Characteristics

Vcc=28V. Resistive load=6.8Ω. Ti=25°C

| Symbol | Parameter | Min. | Тур. | Max. | Units | Test Conditions |
|--------|----------------------------------|------|------|------|-------|-----------------|
| tdon | Turn on delay time | 6 | 15 | 30 | 110 | |
| tr | Rise time from 20% to 80% of Vcc | 5 | 10 | 30 | μs | See fig. 1 |
| tdoff | Turn off delay time | 25 | 50 | 100 | | See lig. I |
| tf | Fall time from 80% to 20% of Vcc | 6 | 15 | 30 | μs | |

Protection Characteristics

Ti=25°C. Vcc=28V (unless otherwise specified)

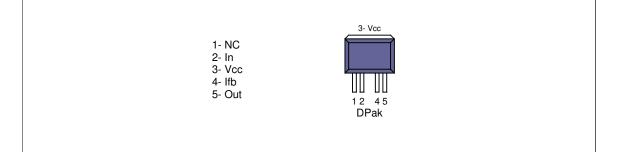
| Symbol | Parameter | Min. | Тур. | Max. | Units | Test Conditions |
|---------|--|------|------|------|-------|------------------------|
| Tsd | Over temperature threshold(2) | 150 | 165 | _ | °C | See fig. 3 and fig. 11 |
| lsd | Over-current shutdown | 50 | 60 | 80 | А | See fig. 3 and page 7 |
| I fault | Ifb after an over-current or an over- temperature (latched) | 2.7 | 3.3 | 4 | mA | See fig. 3 |

Current Sensing Characteristics Tj=25°C, Vcc=28V (unless otherwise specified), Vcc-Vifb>4V

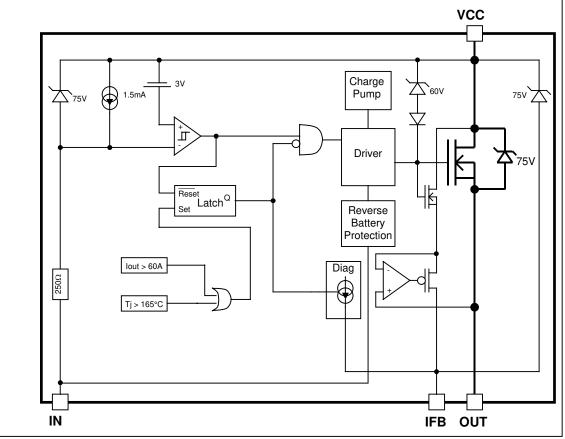
| Symbol | Parameter | Min. | Тур. | Max. | Units | Test Conditions |
|-------------|--|------|------|------|-------|--------------------|
| Ratio | I load / Ifb current ratio | 7050 | 8500 | 9950 | | lload=5A |
| Ratio_TC | I load / Ifb variation over temperature(2) | -5% | 0 | +5 | % | Tj=-40°C to +150°C |
| I offset | Load current offset | -0.6 | 0 | 0.6 | Α | lout<5A |
| Ifb leakage | Ifb leakage current | 0 | 10 | 100 | μA | lout=0A |

(2) Guaranteed by design

Lead Assignments



Functional Block Diagram



International

Truth Table

| Op. Conditions | Input | Output | Ifb pin voltage |
|----------------------|-------|--------|--------------------------|
| Normal mode | Н | L | 0V |
| Normal mode | L | Н | I load x Rfb / Ratio |
| Open load | Н | L | 0V |
| Open load | L | Н | Ifb leakage x Rifb |
| Short circuit to GND | H | L | 0V |
| Short circuit to GND | L | L | I fault x Rifb(latched) |
| Over temperature | H | L | 0V |
| Over temperature | L | L | I fault x Rifb (latched) |

Operating voltage

Maximum Vcc voltage : this is the maximum voltage before the breakdown of the IC process. **Operating voltage** : This is the Vcc range in which the functionality of the part is guaranteed. The AEC-Q100 qualification is run at the maximum operating voltage specified in the datasheet.

Reverse battery

During the reverse battery the Mosfet is turned on if the input pin is powered with a diode in parallel of the input transistor. Power dissipation in the IPS : $P = Rdson rev * I load^2 + Vcc^2 / 250$ (internal input resistor). If the power dissipation is too high in Rifb, a diode in serial can be added to block the current.

Active clamp

The purpose of the active clamp is to limit the voltage across the MOSFET to a value below the body diode break down voltage to reduce the amount of stress on the device during switching.

The temperature increase during active clamp can be estimated as follows:

 $\Delta_{Tj} = \mathbf{P}_{CL} \cdot \mathbf{Z}_{TH}(\mathbf{t}_{CLAMP})$

Where: $Z_{TH}(t_{CLAMP})$ is the thermal impedance at t_{CLAMP} and can be read from the thermal impedance curves given in the data sheets.

 $P_{CL} = V_{CL} \cdot I_{CLava}$: Power dissipation during active clamp

 $V_{CL} = 65V$: Typical V_{CLAMP} value

$$\begin{split} I_{CLavg} &= \frac{I_{CL}}{2}: \text{Average current during active clamp} \\ t_{CL} &= \frac{I_{CL}}{\left|\frac{di}{dt}\right|}: \text{Active clamp duration} \\ \frac{di}{dt} &= \frac{V_{Battery} - V_{CL}}{L}: \text{Demagnetization current} \end{split}$$

Figure 9 gives the maximum inductance versus the load current in the worst case : the part switches off after an over temperature detection. If the load inductance exceeds the curve, a free wheeling diode is required.

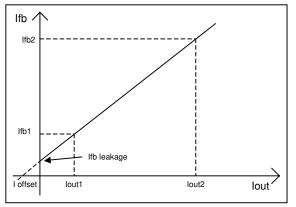
Over-current protection

The threshold of the over-current protection is set in order to guarantee that the device is able to turn on a load with an inrush current lower than the minimum of Isd. Nevertheless for high current and high temperature the device may switch off for a lower current due to the over-temperature protection. This behavior is shown in Figure 11.

International

AUIPS7121R

Current sensing accuracy



The current sensing is specified by measuring 3 points :

- Ifb1 for lout1

- Ifb2 for lout2

- Ifb leakage for lout=0

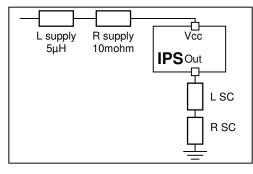
The parameters in the datasheet are computed with the following formula : Ratio = (lout2 - lout1)/(lfb2 - lfb1) l offset = lfb1 x Ratio - lout1

This allows the designer to evaluate the lfb for any lout value using : lfb = (lout + l offset) / Ratio if lfb > lfb leakage

For some applications, a calibration is required. In that case, the accuracy of the system will depends on the variation of the I offset and the ratio over the temperature range. The ratio variation is given by Ratio_TC specified in page 4. The loffset variation depends directly on the Rdson : I offset@-40°C= I offset@25°C / 0.8 I offset@150°C= I offset@25°C / 1.9

Maximum Vcc voltage with short circuit protection

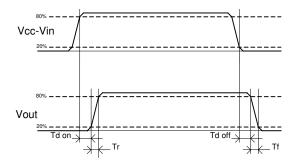
The maximum Vcc voltage with short circuit is the maximum voltage for which the part is able to protect itself under test conditions representative of the application. 2 kind of short circuits are considered : terminal and load short circuit.



| | L SC | R SC |
|-------------|--------|----------|
| Terminal SC | 0.1 μH | 10 mohm |
| Load SC | 10 µH | 100 mohm |

International

AUIPS7121R



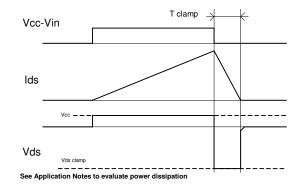


Figure 1 – IN rise time & switching definitions

Figure 2 – Active clamp waveforms

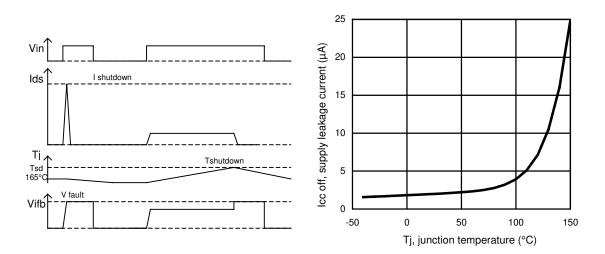


Figure 3 – Protection timing diagram

Figure 4 – Icc off (µA) Vs Tj (°C)

International

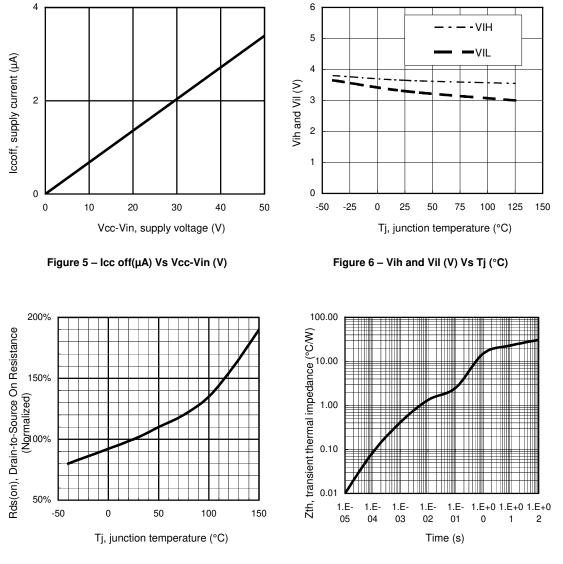


Figure 7 - Normalized Rds(on) (%) Vs Tj (°C)

Figure 8 – Transient thermal impedance (°C/W) Vs time (s)

International

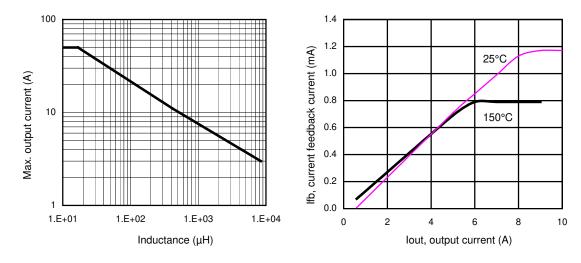
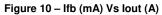
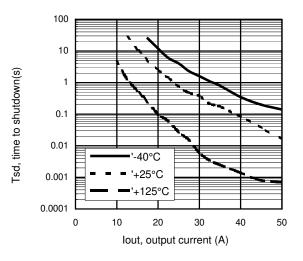
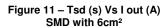


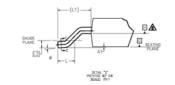
Figure 9 – Max. lout (A) Vs inductance (µH)

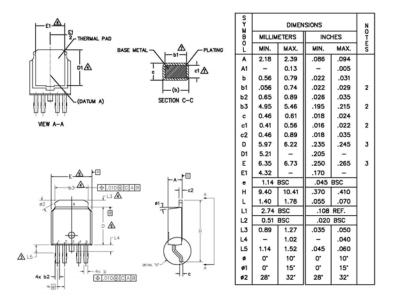






Case Outline 5 Lead – DPAK





NOTES:

1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M-1994

2 .- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].

A- LEAD DIMENSION UNCONTROLLED IN L5.

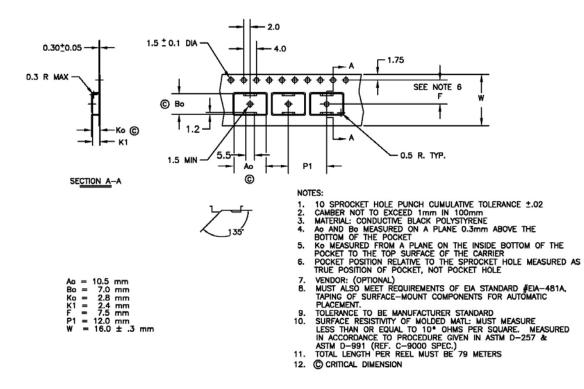
- A- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.

A- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.

- 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252.
- 10. LEADS AND DRAIN ARE PLATED WITH 100% Sn

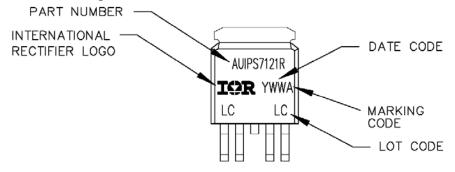
International

Tape & Reel 5 Lead – DPAK



International

Part Marking Information



Ordering Information

| Base Part Number | De che un Trucc | Standard Pack | | Ormalista David Namehou |
|------------------|-----------------|---------------------|----------|-------------------------|
| Dase Part Number | Package Type | Form | Quantity | Complete Part Number |
| | | Tube | 75 | AUIPS7121R |
| AUIPS7121R | D-Pak-5-Lead | Tape and reel | 3000 | AUIPS7121RTR |
| AUFS/12Th | D-Fak-3-Leau | Tape and reel left | 2000 | AUIPS7121RTRL |
| | | Tape and reel right | 2000 | AUIPS7121RTRR |

The information provided in this document is believed to be accurate and reliable. However, International Rectifier assumes no responsibility for the consequences of the use of this information. International Rectifier assumes no responsibility for any infringement of patents or of other rights of third parties which may result from the use of this information. No license is granted by implication or otherwise under any patent or patent rights of International Rectifier. The specifications mentioned in this document are subject to change without notice. This document supersedes and replaces all information previously supplied.

For technical support, please contact IR's Technical Assistance Center http://www.irf.com/technical-info/

> WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105